GaAs single quantum dot embedded into AlGaAs nanowire.

A .V. Platonov V.N. Kats, V.P. Kochereshko, T.V. Chizhova,

G.E. Cirlin, A.D. Bouravleuv, Yu.B. Samsonenko, I.P.Soshnikov Ioffe Institute and St. Petersburg Academic University

J. Bleuse, L.Besombes, H. Mariette CEA-CNRS group "Nanophysique et Semiconducteurs", CEA, INAC, SP2M, and Institut Néel

D. Barettin, A. Pecchia, M. Auf der Maur, A. Di Carlo University of Rome Tor Vergata







Outline

- Sample details
- Motivation
- Micro-PL on the single QD spectrocopy
 - Exciton and Exciton complexes in QD
 - PL polarization
 - Line broadening due to the spectral diffusion
 - Micro PLE data from the single QD
- Numerical simulation of the optical spectra. The role of the strain and piezoelectric effect.
- Time resolved PL spectra of the single QD.
- Conclusions

Catalyst assisted MBE growth



30-60 nm

QD insertion



By closing the Al source for the short time we can produce pure GaAs layer within the nanowire.

This gives a way to insert the single QD or the QD chain into the nanowire.

The QD shape is defined by the NW geometry and its height is controllable with monolayer precision.

TEM and SEM images



•QD height 5 nm and its diameter 20-30nm•Sharp interfaces



•Wurzite crystal phase => strong piezoelectric effect

Motivation



- •QD with well controllable size and well defined shape
- •The dots in nanowire can be contacted electrically
- •Opportunity to produce the QD chain, which has a controllable overlap

Specific vibration modes



New field for the phonon spectroscopy

+ strong piezoelectric effect => high efficient acoustic transmitter and receiver in wide band
Radio frequency - realized
THz - probably realized
10-100 GHz - under consideration

$\mu\text{-}\text{PL}$ measurements of the single QD



Excitation and registration occurs along the wire. Normal geometry Only few NW catch the aperture that allows to operate with the single NW within ensemble.

PL spectra of the single QD in NW



Exciton, trion and biexciton are observed
PL spectra show a strong linear polarization
Line width is extremely large for the single QD

Spectral diffusion



•At very low excitation power the line width decreases by the order of magnitude

•The line position changes for the discrete values.

•Jump rate increases by the increase of the power finally giving the broad line.

•The effect of the spectral diffusion can be explained by taking into account the possible charging of some deep states that can surround the QD.

PLE spectra from the single QD in NW



Numerical calculation of the energy states Comparison with experiment data



Good coincidence between experimental and simulated data allows us to assume the model adequacy

Numerical simulation of the PL polarization



The model allows to consider the strain and electric filed. Both effects having minor influence on the state position give the pronounced polarization ratio. However its order of magnitude less then the observed one.

Time resolved µ-PL



QD PL decay time 5 ns -----long capturing time

Conclusions

- Photoluminescence spectra from the single QD/NW GaAs/AlGaAs structure have been measured.
- Optical transitions related to the exciton and exciton complexes are observed.
- The effect of the spectral diffusion is detected and explained.
- The strong PL polarization along symmetrical axes is found.
- Numerical simulation of the optical spectra is performed.
- The role of the strain and electric on the optical polarization is discussed.